■ **Electrical Characteristics** (T_J=25 unless otherwise noted)

Parameter	**Symbol**	**Conditions**	**Min**	**Typ**	**Max**	**Units**
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}= 0V, I_D=250μA	100	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=100V, V_{GS}=0V	-	-	1	μA
		V_{DS}=100V, V_{GS}=0V, Tj=150	-	-	100	
Gate-Body Leakage Current	I_{GSS}	V_{GS}= ±20V, V_{DS}=0V	-	-	±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}= V_{GS}, I_D=250μA	1	1.8	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=60A	-	3.2	4	mΩ

Typical Electrical and Thermal Characteristics Diagrams

Figure1. Output Characteristics

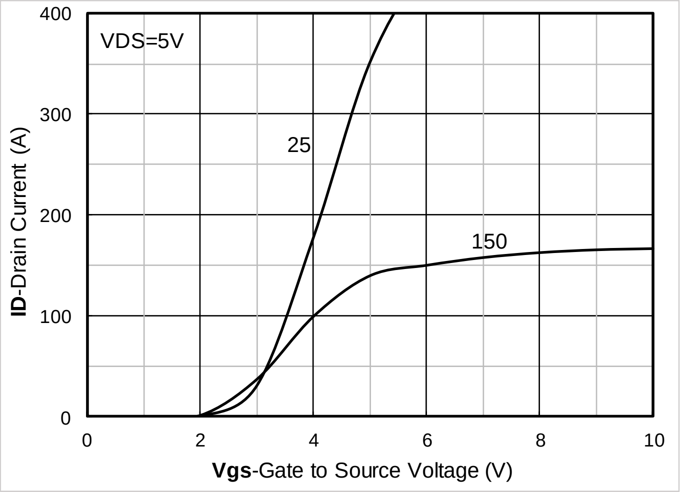
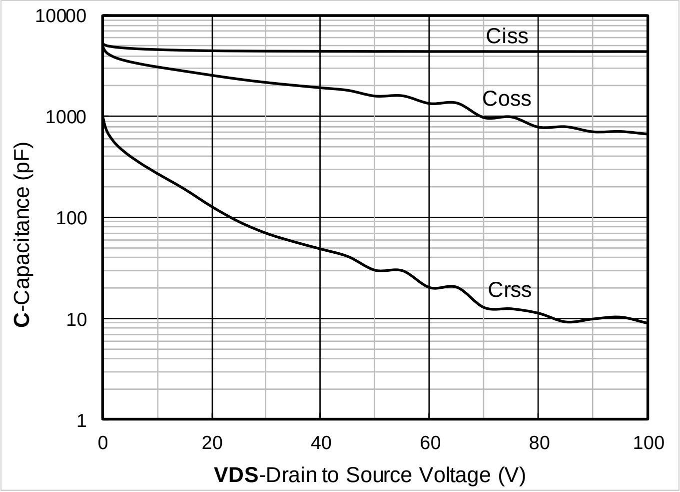
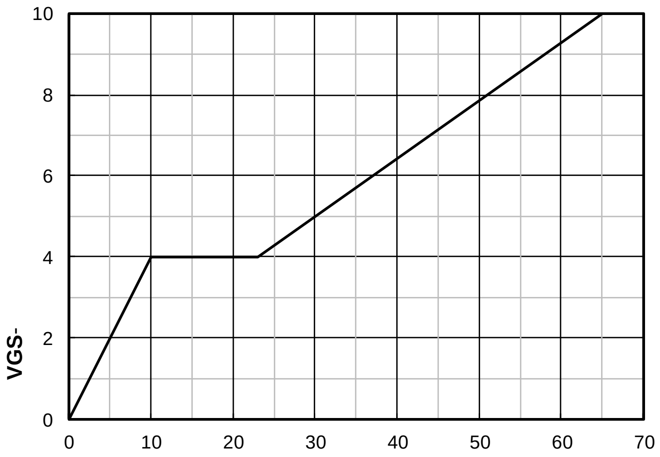


Figure2. Transfer Characteristics





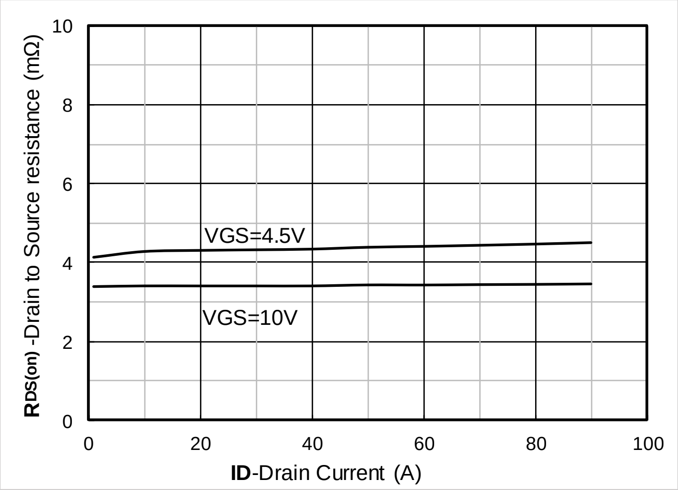


Figure7. RDS(on) VS Drain Current

Figure8. Forward characteristics of reverse diode

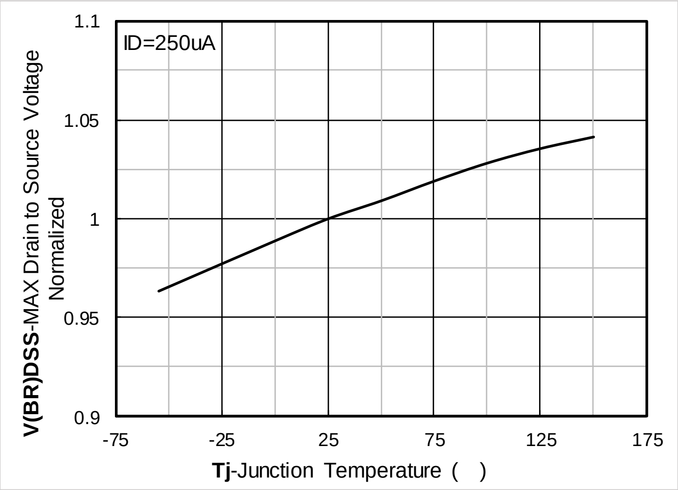


Figure9. Normalized breakdown voltage

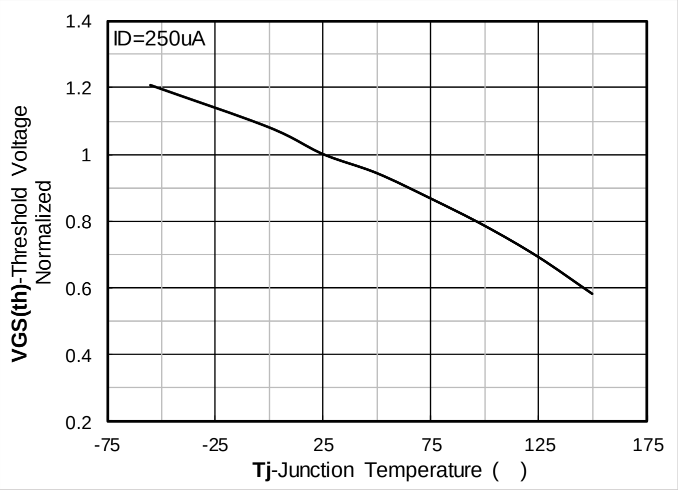


Figure10. Normalized Threshold voltage

Figure11. Current dissipation

Figure12. Power dissipation

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The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of with would directly endanger human life (81(w)h90.94 Tm